

PIM with Trench Field-Stop IGBT, Emitter Controlled Diode and NTC

Features

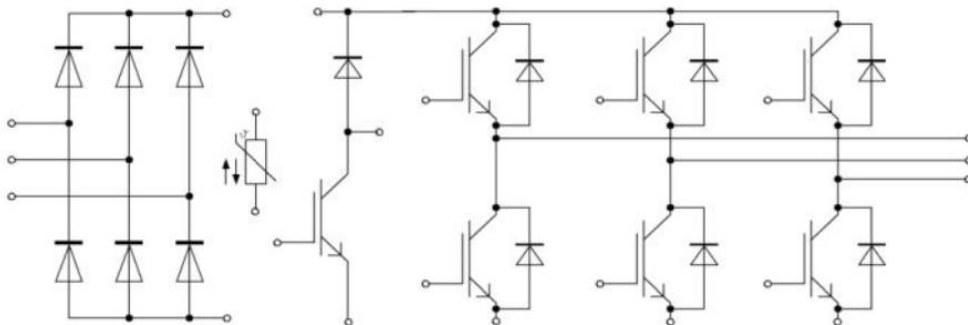
- Trench+ Field Stop Technology
- 1200V Trench Field-Stop IGBT
- Low $V_{CE(sat)}$ with Low Switching Losses

Applications

- Frequency Converters
- Motor Drives
- Auxiliary Inverters



Equivalent Circuit Schematic



IGBT - Inverter

Maximum Rated Values

Symbol	Description	Conditions	Values	Unit
V_{CES}	Collector-Emitter Voltage	$T_{vj}=25^{\circ}C$	1200	V
V_{GES}	Gate-Emitter Peak Voltage	$T_{vj}=25^{\circ}C$	± 20	V
I_C	Continuous DC Collector Current	$T_C=100^{\circ}C$	25	A
I_{CRM}	Repetitive Peak Collector Current	$t_p=1ms$	50	A
P_{tot}	Total Power Dissipation	$T_C=25^{\circ}C, T_{vj\ max}=175^{\circ}C$	153	W

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15V, I_C=25A, T_{vj}=25^{\circ}C$	---	2.24	---	V
		$V_{GE}=15V, I_C=25A, T_{vj}=125^{\circ}C$	---	2.70	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE}=V_{CE}, I_C=0.8mA$		5.5		V
I_{CES}	Collector-Emitter Cut-Off Current	$V_{CE}=1200V, V_{GE}=0V$	---	---	1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=20V, V_{CE}=0V$	---	---	100	nA
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1MHz$	---	1850	---	pF
C_{oes}	Output Capacitance		---	145	---	pF
C_{res}	Reverse Transfer Capacitance		---	60	---	pF
$t_{d(on)}$	Turn-on Delay Time	$V_{CE}=600V$ $V_{GE}=\pm 15V$ $I_C=25A$ $R_G=20\Omega$ Inductive Load $T_{vj}=25^{\circ}C$	---	21	---	ns
t_r	Turn-on Rise Time		---	31	---	ns
$t_{d(off)}$	Turn-off Delay Time		---	196	---	ns
t_f	Turn-off Fall Time		---	267	---	ns
E_{on}	Turn-on Switching Loss		---	1.62	---	mJ
E_{off}	Turn-off Switching Loss		---	2.83	---	mJ
I_{SC}	Short Circuit data	$V_{GE}\leq 15V, V_{CC}=800V$ $t_p\leq 10\mu s, T_{vj}=150^{\circ}C$	---	92	---	A
R_{thJC}	Thermal Resistance, Junction to Case	Per IGBT	---	---	0.98	K/W
T_{VJOP}	Virtual Junction Temperature	Under Switching	-40	---	150	$^{\circ}C$

**Diode - Inverter
Maximum Rated Values**

Symbol	Description	Conditions	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25^{\circ}C$	1200	V
I_F	Continuous DC Forward Current		30	A
I_{FRM}	Repetitive Peak Collector Current	$t_p=1ms$	60	A

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _F	Forward Voltage	I _F =30A, V _{GE} =0V, T _{vj} =25°C	---	2.27	---	V
		I _F =30A, V _{GE} =0V, T _{vj} =125°C	---	1.94	---	V
I _{RM}	Peak Reverse Recovery Current	I _F =25A, V _R =600V, V _{GE} =-15V T _{vj} =25°C	---	38	---	A
Q _r	Recovered Charge		---	1.2	---	uC
E _{rec}	Reverse Recovery Energy		---	0.2	---	mJ
R _{thJC}	Thermal Resistance, Junction to Case	Per Diode	---	---	1.3	K/W
T _{VJ OP}	Virtual Junction Temperature	Under Switching	-40	---	150	°C

**Diode - Rectifier
Maximum Rated Values**

Symbol	Description	Conditions	Values	Unit
V _{RRM}	Repetitive Peak Reverse Voltage	T _{vj} =25°C	1600	V
I _{F(AV)}	Average Output Current	T _{vj} =25°C	30	A
I _{FSM}	Surge Forward Current	t _p =10ms, sin180°, T _J =25°C	360	A
I ² t	I ² t Value	t _p =10ms, sin180°, T _J =25°C	648	A ² s

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
V _F	Forward Voltage	I _F =30A, V _{GE} =0V, T _{vj} =25°C	---	1.0	---	V
I _R	Recovery Current	V _R =1600V, T _{vj} =25°C	---	5	---	uA
T _{VJ OP}	Virtual Junction Temperature	Under Switching	-40	---	150	°C

IGBT – Brake

Maximum Rated Values

Symbol	Description	Conditions	Values	Unit
V_{CES}	Collector-Emitter Voltage	$T_{vj}=25^{\circ}\text{C}$	1200	V
V_{GES}	Gate-Emitter Peak Voltage	$T_{vj}=25^{\circ}\text{C}$	± 20	V
I_C	Continuous DC Collector Current	$T_C=100^{\circ}\text{C}$	25	A
I_{CRM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	50	A

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}, I_C=25\text{A}, T_{vj}=25^{\circ}\text{C}$	---	2.17	--	V
		$V_{GE}=15\text{V}, I_C=25\text{A}, T_{vj}=125^{\circ}\text{C}$	---	2.60	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE}=V_{CE}, I_C=0.8\text{mA}$	---	5.6	---	V
I_{CES}	Collector-Emitter Cut-Off Current	$V_{CE}=1200\text{V}, V_{GE}=0\text{V}$	---	---	1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=20\text{V}, V_{CE}=0\text{V}$	---	---	100	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	---	1840	---	pF
C_{oes}	Output Capacitance		---	85	---	pF
C_{res}	Reverse Transfer Capacitance		---	60	---	pF
$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}$ $V_{GE}=\pm 15\text{V}$ $I_C=25\text{A}$ $R_G=20\Omega$ Inductive Load $T_{vj}=25^{\circ}\text{C}$	---	20	---	ns
t_r	Turn-on Rise Time		---	37	---	ns
$t_{d(off)}$	Turn-off Delay Time		---	190	---	ns
t_f	Turn-off Fall Time		---	260	---	ns
E_{on}	Turn-on Switching Loss		---	1.6	---	mJ
E_{off}	Turn-off Switching Loss		---	2.7	---	mJ
I_{SC}	Short Circuit Data	$V_{GE}\leq 15\text{V}, V_{CC}=800\text{V}$ $t_p\leq 10\mu\text{s}, T_{vj}=25^{\circ}\text{C}$	---	92	---	A
T_{VJOP}	Virtual Junction Temperature	Under Switching	-40	---	150	$^{\circ}\text{C}$

Diode - Brake

Maximum Rated Values

Symbol	Description	Conditions	Values	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25^{\circ}\text{C}$	1200	V
I_F	Continuous DC Forward Current		15	A
I_{FRM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	30	A

Characteristic Values

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
V_F	Forward Voltage	$I_F=15\text{A}, V_{GE}=0\text{V}, T_{vj}=25^{\circ}\text{C}$	---	2.06	---	V
		$I_F=15\text{A}, V_{GE}=0\text{V}, T_{vj}=125^{\circ}\text{C}$	---	1.65	---	V
I_{RM}	Peak Reverse Recovery Current	$I_F=15\text{A}, V_R=600\text{V}, V_{GE}=-15\text{V}$ $T_{vj}=25^{\circ}\text{C}$	---	18	---	A
Q_r	Recovered Charge		---	1.8	---	μC
E_{rec}	Reverse Recovery Energy		---	0.68	---	mJ
T_{VJOP}	Virtual Junction Temperature	Under Switching	-40	---	150	$^{\circ}\text{C}$

NTC-Thermistor

Characteristic Values

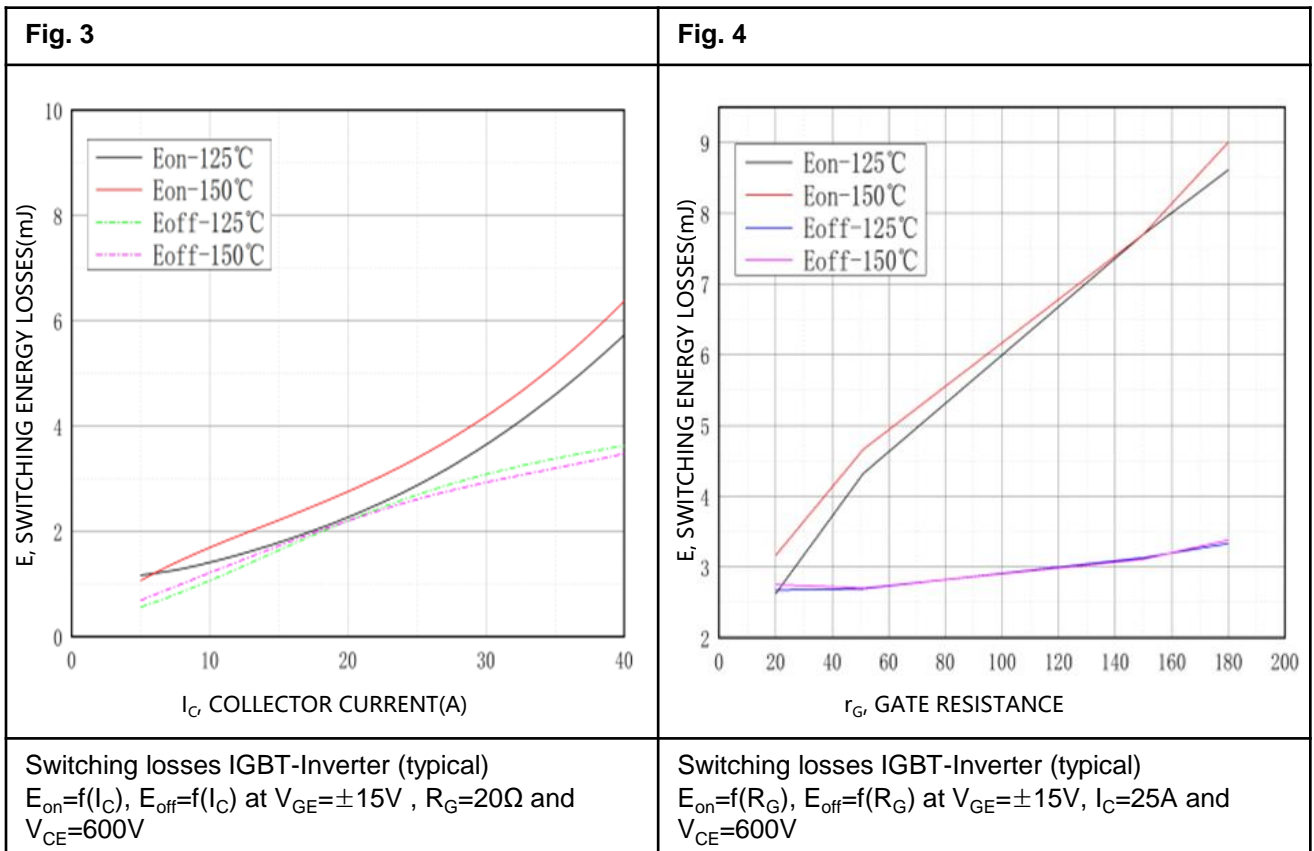
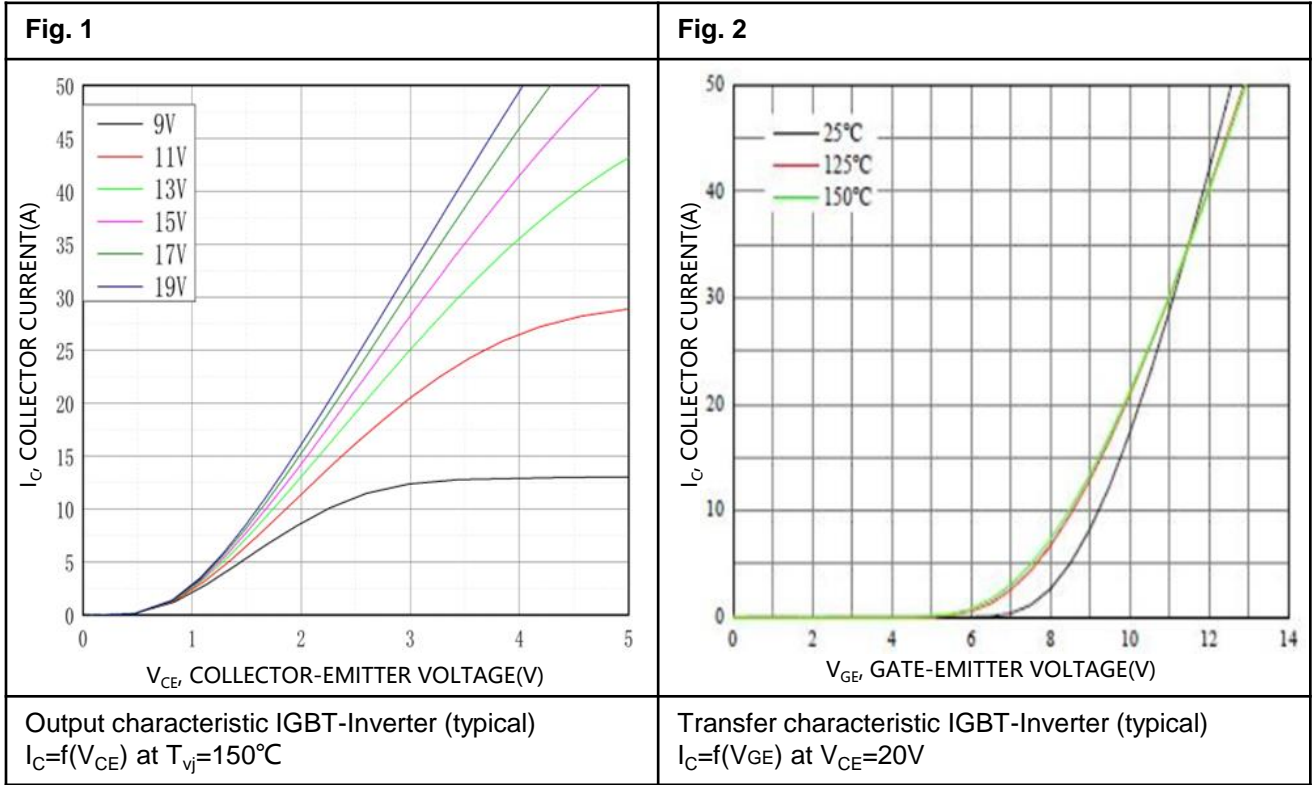
Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
R_{25}	Rated Resistance	$T_C=25^{\circ}\text{C}$	---	5	---	$\text{K}\Omega$
$B_{25/50}$	B Value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298 \text{ K}))]$	---	3380	---	K

Module

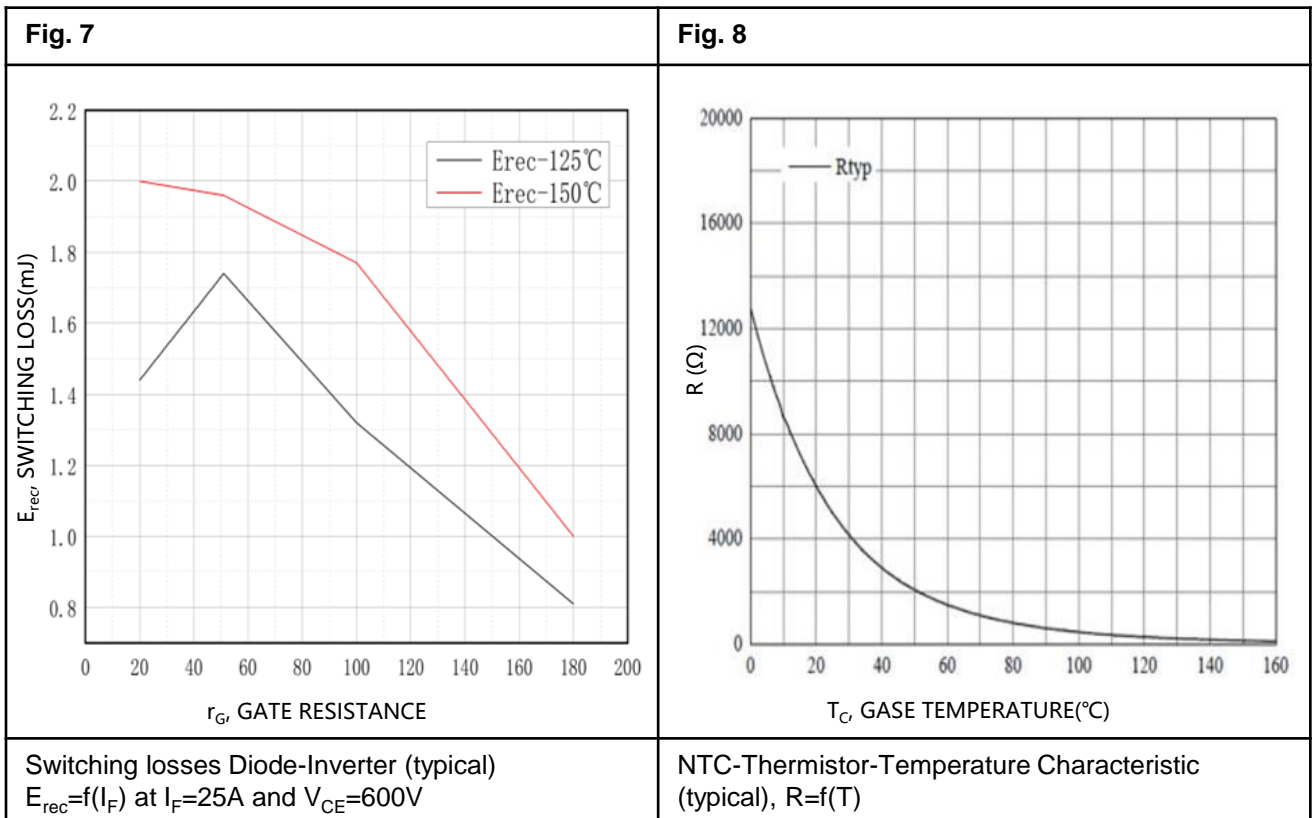
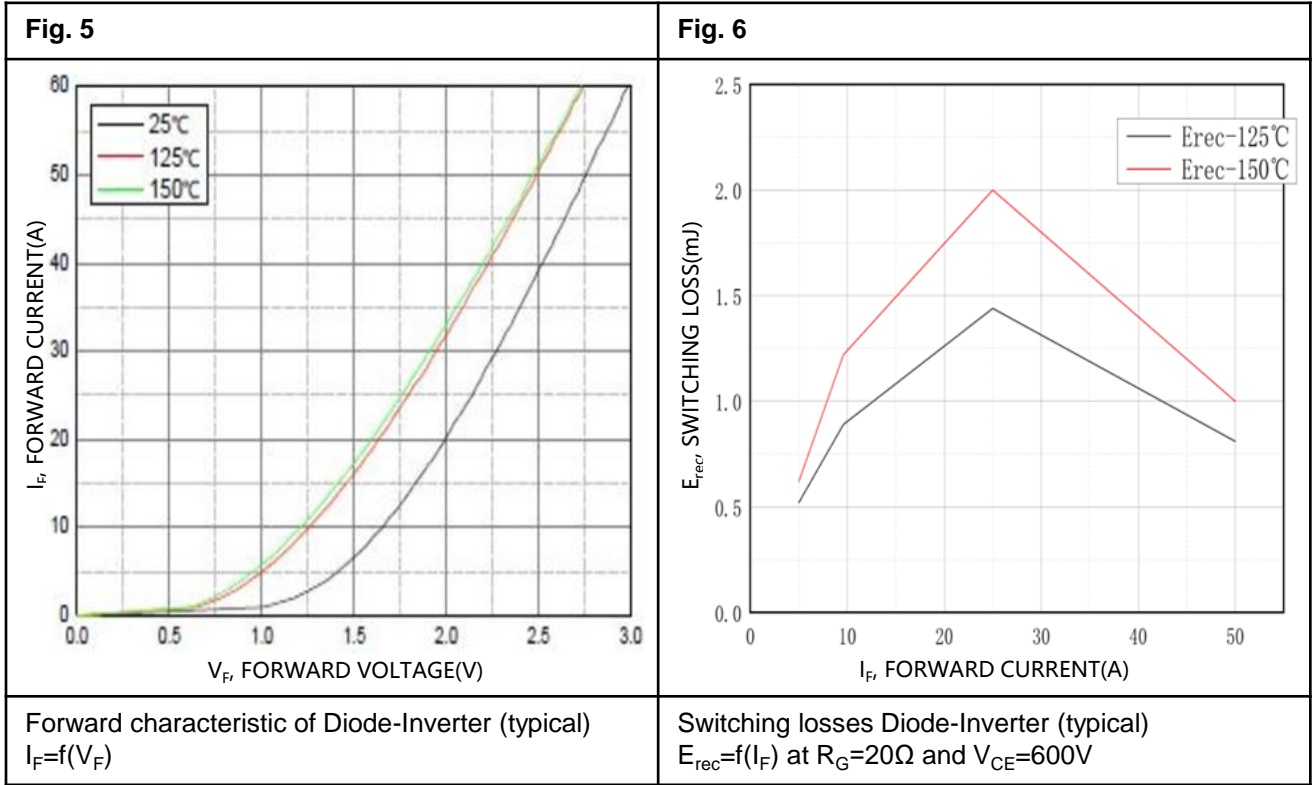
Symbol	Description	Conditions	Values	Unit
V _{ISOL}	Isolation Test Voltage	RMS, f=50Hz, t=1min	3	KV
	Internal Isolation	Basic Insulation (Class 1, IEC 61140)	Al ₂ O ₃	
	Creepage Distance	Terminal to Heatsink	11.8	mm
		Terminal to Terminal	6	
	Clearance	Terminal to Heatsink	10.2	mm
		Terminal to Terminal	5.1	

Symbol	Description	Conditions	Values			Unit
			Min.	Typ.	Max.	
L _{sCE}	Stray Inductance Module		---	30	---	nH
T _{stg}	Storage Temperature		-40	---	125	°C
R _{CC+EE'}	Module Lead Resistance, Terminals-chip		---	8.0	---	mΩ
G	Weight		---	39	---	g

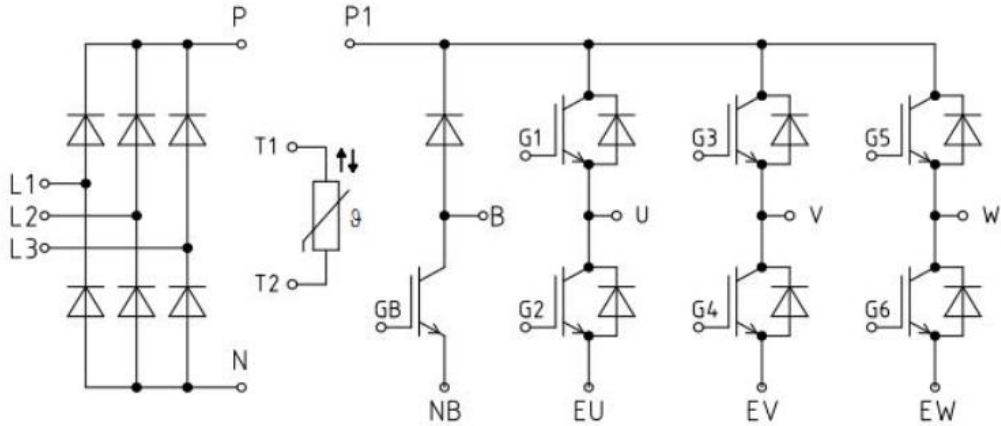
Typical Characteristics



Typical Characteristics



Circuit Diagram



Package Outlines (mm)

